Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 plastic package intended for use in applications requiring high bidirectional blocking voltage capability, high surge current capability and high thermal cycling performance.

2. Features and benefits

- · High bidirectional blocking voltage capability
- High surge current capability
- · High thermal cycling performance

3. Applications

- · Ignition circuits
- Motor control
- Protection circuits
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
V_{RRM}	repetitive peak reverse voltage		-	-	800	V
I _{TSM} non-repetitive peak onstate current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	-	120	Α	
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	-	132	Α
Tj	junction temperature		-	-	125	°C
$I_{T(AV)}$	average on-state current	half sine wave; T _{mb} ≤ 109 °C; <u>Fig. 1</u>	-	-	7.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 109 ^{\circ}\text{C}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$	-	-	12	Α
Static chara	cteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _i = 25 °C; <u>Fig. 7</u>	-	2	15	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; R_{GK} = 100 Ω; (V_{DM} = 67% of V_{DRM}); exponential waveform; Fig. 12	200	1000	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	А - [-] К
2	Α	anode		G sym037
3	G	gate		Symosi
mb	A	mounting base; connected to anode		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT151-800R	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

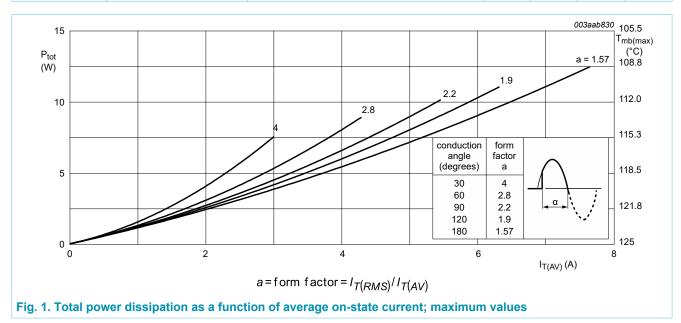
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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 109 °C; <u>Fig. 1</u>	-	7.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 109 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	12	A
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5	-	120	Α
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms	-	132	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	72	A²s
dl _T /dt	rate of rise of on-state current	I _G = 30 mA	-	50	A/µs
I _{GM}	peak gate current		-	2	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C



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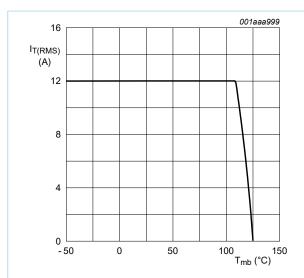


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

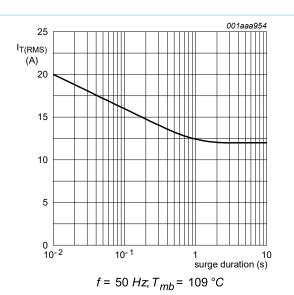


Fig. 3. RMS on-state current as a function of surge duration; maximum values

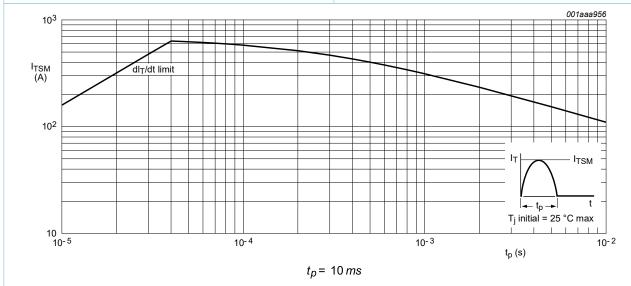


Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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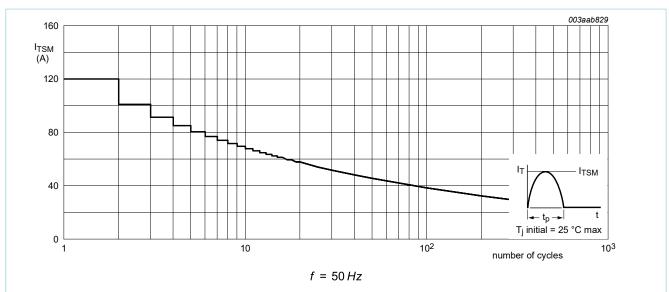


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	1.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

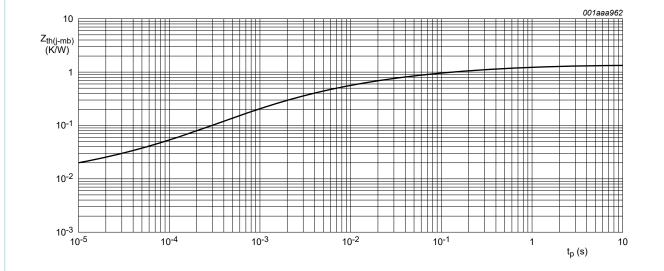


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			,
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u>	-	2	15	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	10	40	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	7	20	mA
V _T	on-state voltage	I _T = 23 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.75	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.6	1.5	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
I _R	reverse current	V _R = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	haracteristics		,			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_{j} = 125 °C; R_{GK} = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 12	200	1000	-	V/µs
		V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	50	130	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 800 V; I_G = 0.1 A; dI_G/dt = 5 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 536 V; T_j = 125 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/ μ s; dV_D/dt = 50 V/ μ s; $R_{GK(ext)}$ = 100 Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	70	-	μs

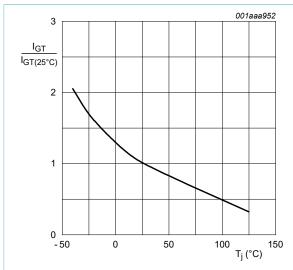


Fig. 7. Normalized gate trigger current as a function of junction temperature

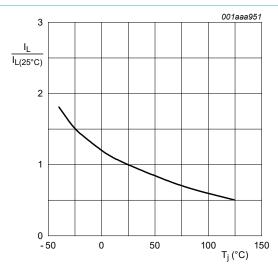


Fig. 8. Normalized latching current as a function of junction temperature

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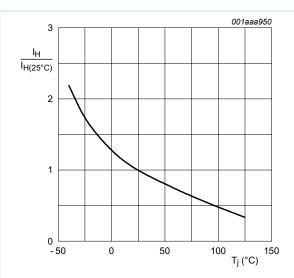
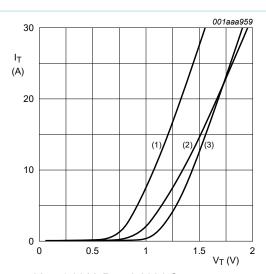


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.06 V; R_s = 0.0304 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

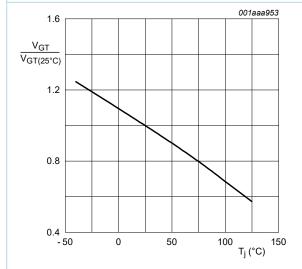
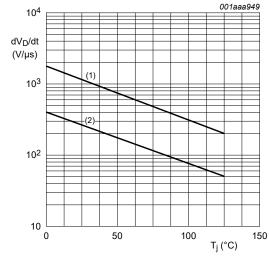


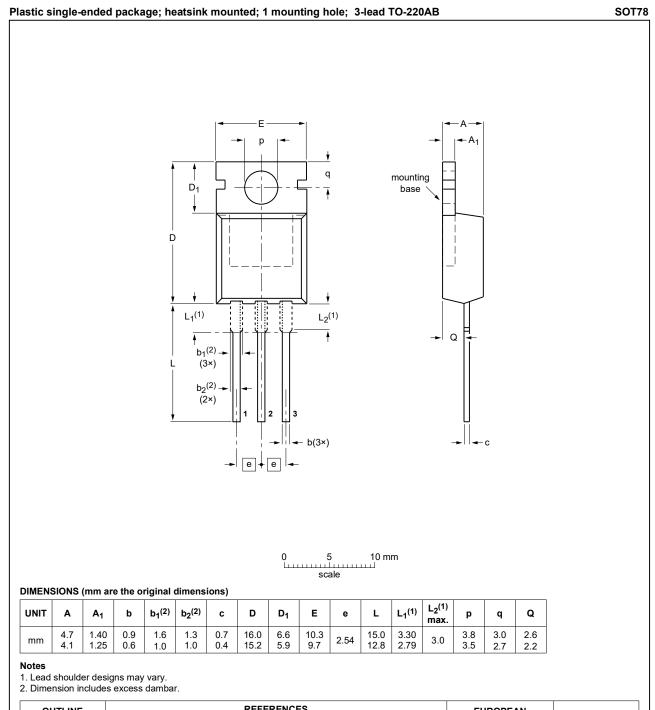
Fig. 11. Normalized gate trigger voltage as a function of junction temperature



(1) $R_{GK} = 100 \Omega$; (2) gate open circuit

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

10. Package outline



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

Fig. 13. Package outline TO-220AB (SOT78)

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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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